

Angelica Azcatl

List of Publications by Year in descending order

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32
papers

5,113
citations

236925

25
h-index

454955

30
g-index

32
all docs

32
docs citations

32
times ranked

8701
citing authors

#	ARTICLE	IF	CITATIONS
1	Near-unity photoluminescence quantum yield in MoS ₂ . Science, 2015, 350, 1065-1068.	12.6	993
2	MoS ₂ P-type Transistors and Diodes Enabled by High Work Function MoO _x Contacts. Nano Letters, 2014, 14, 1337-1342.	9.1	487
3	Hole Selective MoO _x Contact for Silicon Solar Cells. Nano Letters, 2014, 14, 967-971.	9.1	476
4	Manganese Doping of Monolayer MoS ₂ : The Substrate Is Critical. Nano Letters, 2015, 15, 6586-6591.	9.1	357
5	Highly Scalable, Atomically Thin WSe ₂ Grown <i>via</i> Metal-Organic Chemical Vapor Deposition. ACS Nano, 2015, 9, 2080-2087.	14.6	339
6	Covalent Nitrogen Doping and Compressive Strain in MoS ₂ by Remote N ₂ Plasma Exposure. Nano Letters, 2016, 16, 5437-5443.	9.1	323
7	Impurities and Electronic Property Variations of Natural MoS ₂ Crystal Surfaces. ACS Nano, 2015, 9, 9124-9133.	14.6	240
8	HfO ₂ on MoS ₂ by Atomic Layer Deposition: Adsorption Mechanisms and Thickness Scalability. ACS Nano, 2013, 7, 10354-10361.	14.6	237
9	HfSe ₂ Thin Films: 2D Transition Metal Dichalcogenides Grown by Molecular Beam Epitaxy. ACS Nano, 2015, 9, 474-480.	14.6	195
10	Hole Contacts on Transition Metal Dichalcogenides: Interface Chemistry and Band Alignments. ACS Nano, 2014, 8, 6265-6272.	14.6	173
11	MoS ₂ functionalization for ultra-thin atomic layer deposited dielectrics. Applied Physics Letters, 2014, 104, .	3.3	171
12	Remote Plasma Oxidation and Atomic Layer Etching of MoS ₂ . ACS Applied Materials & Interfaces, 2016, 8, 19119-19126.	8.0	145
13	Comprehensive structural and optical characterization of MBE grown MoSe ₂ on graphite, CaF ₂ and graphene. 2D Materials, 2015, 2, 024007.	4.4	120
14	Atomic Layer Deposition of a High- <i>k</i> Dielectric on MoS ₂ Using Trimethylaluminum and Ozone. ACS Applied Materials & Interfaces, 2014, 6, 11834-11838.	8.0	105
15	HfO ₂ on UV ^o O ₃ exposed transition metal dichalcogenides: interfacial reactions study. 2D Materials, 2015, 2, 014004.	4.4	98
16	Controllable growth of layered selenide and telluride heterostructures and superlattices using molecular beam epitaxy. Journal of Materials Research, 2016, 31, 900-910.	2.6	85
17	Partially Fluorinated Graphene: Structural and Electrical Characterization. ACS Applied Materials & Interfaces, 2016, 8, 5002-5008.	8.0	82
18	Al ₂ O ₃ on Black Phosphorus by Atomic Layer Deposition: An <i>in Situ</i> Interface Study. ACS Applied Materials & Interfaces, 2015, 7, 13038-13043.	8.0	81

#	ARTICLE	IF	CITATIONS
19	Evaluation of border traps and interface traps in HfO ₂ /MoS ₂ gate stacks by capacitance-voltage analysis. 2D Materials, 2018, 5, 031002.	4.4	63
20	Improvement in top-gate MoS ₂ transistor performance due to high quality backside Al ₂ O ₃ layer. Applied Physics Letters, 2017, 111, .	3.3	56
21	MBE growth of few-layer 2H-MoTe ₂ on 3D substrates. Journal of Crystal Growth, 2018, 482, 61-69.	1.5	43
22	Superacid Passivation of Crystalline Silicon Surfaces. ACS Applied Materials & Interfaces, 2016, 8, 24205-24211.	8.0	38
23	Probing Interface Defects in Top-Gated MoS ₂ Transistors with Impedance Spectroscopy. ACS Applied Materials & Interfaces, 2017, 9, 24348-24356.	8.0	38
24	Schottky Barrier Height of Pd/MoS ₂ Contact by Large Area Photoemission Spectroscopy. ACS Applied Materials & Interfaces, 2017, 9, 38977-38983.	8.0	36
25	Effects of annealing on top-gated MoS ₂ transistors with HfO ₂ dielectric. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	31
26	Electrical characterization of top-gated molybdenum disulfide field-effect-transistors with high-k dielectrics. Microelectronic Engineering, 2017, 178, 190-193.	2.4	26
27	A comparative study of atomic layer deposition of Al ₂ O ₃ and HfO ₂ on AlGaIn/GaN. Journal of Materials Science: Materials in Electronics, 2015, 26, 4638-4643.	2.2	25
28	<i>In situ</i> x-ray photoelectron spectroscopy and capacitance voltage characterization of plasma treatments for Al ₂ O ₃ /AlGaIn/GaN stacks. Applied Physics Letters, 2014, 105, .	3.3	20
29	Surface and interfacial study of half cycle atomic layer deposited Al ₂ O ₃ on black phosphorus. Microelectronic Engineering, 2015, 147, 1-4.	2.4	15
30	Al ₂ O ₃ on WSe ₂ by ozone based atomic layer deposition: Nucleation and interface study. APL Materials, 2017, 5, .	5.1	11
31	Top-gated MoS ₂ capacitors and transistors with high-k dielectrics for interface study. , 2016, , .		3
32	Test structures for understanding the impact of ultra-high vacuum metal deposition on top-gate MoS ₂ field-effect-transistors. , 2017, , .		1